

MOS FIELD EFFECT TRANSISTOR

2SK3433

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK3433 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

• Super low on-state resistance:

RDS(on)1 = $26 \text{ m}\Omega$ MAX. (VGS = 10 V, ID = 20 A)

- ★ RDS(on)2 = 41 m Ω MAX. (Vgs = 4.0 V, ID = 20 A)
 - Low Ciss: Ciss = 1500 pF TYP.
 - Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

| Drain to Source Voltage | Voss | 60 | V |
|---|---|--|---|
| Gate to Source Voltage | Vgss | ±20 | V |
| Drain Current (DC) | ID(DC) | ±40 | Α |
| Drain Current (pulse) Note1 | D(pulse) | ±160 | Α |
| Total Power Dissipation (Tc = 25°C) | PT | 47 | W |
| Total Power Dissipation (T _A = 25°C) | PT | 1.5 | W |
| Channel Temperature | Tch | 150 | °C |
| Storage Temperature | T_{stg} | -55 to +150 | °C |
| Single Avalanche Current Note2 | las | 21 | Α |
| Single Avalanche Energy Note2 | Eas | 44 | mJ |
| | Gate to Source Voltage Drain Current (DC) Drain Current (pulse) Note1 Total Power Dissipation (Tc = 25°C) Total Power Dissipation (TA = 25°C) Channel Temperature Storage Temperature Single Avalanche Current Note2 | Gate to Source Voltage VGSS Drain Current (DC) ID(DC) Drain Current (pulse) Note1 ID(pulse) Total Power Dissipation ($Tc = 25^{\circ}C$) PT Total Power Dissipation ($TA = 25^{\circ}C$) PT Channel Temperature Tch Storage Temperature Tstg Single Avalanche Current Note2 IAS | Gate to Source Voltage V_{GSS} ± 20 Drain Current (DC) $I_{D(DC)}$ ± 40 Drain Current (pulse) Note1 $I_{D(pulse)}$ ± 160 Total Power Dissipation ($T_{C} = 25^{\circ}C$) P_{T} 47 Total Power Dissipation ($T_{A} = 25^{\circ}C$) P_{T} 1.5 Channel Temperature T_{Ch} 150 Storage Temperature T_{Stg} -55 to $+150$ Single Avalanche Current Note2 |

Notes 1. PW \leq 10 μ s, Duty cycle \leq 1 %

2. Starting T_{ch} = 25 °C, R_G = 25 Ω , V_{GS} = 20 V \rightarrow 0 V

THERMAL RESISTANCE

| * | Channel to Case | Rth(ch-C) | 2.66 | °C/W |
|---|--------------------|-----------|------|------|
| | Channel to Ambient | Rth(ch-A) | 83.3 | °C/W |

ORDERING INFORMATION

| PART NUMBER | PACKAGE |
|-------------|-----------|
| 2SK3433 | TO-220AB |
| 2SK3433-S | TO-262 |
| 2SK3433-Z | TO-220SMD |

(TO-220AB)



(TO-262)



(TO-220SMD)



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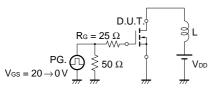
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

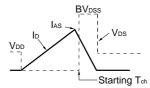


ELECTRICAL CHARACTERISTICS (TA = 25 °C)

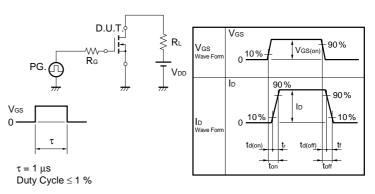
| | CHARACTERISTICS | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|-------------------------------------|----------------------|--|------|------|------|------|
| | Drain to Source On-state Resistance | R _{DS(on)1} | V _{GS} = 10 V, I _D = 20 A | | 22 | 26 | mΩ |
| * | | RDS(on)2 | Vgs = 4.0 V, lb = 20 A | | 29 | 41 | mΩ |
| | Gate to Source Cut-off Voltage | V _{GS(off)} | V _{DS} = 10 V, I _D = 1 mA | 1.5 | 2.0 | 2.5 | V |
| * | Forward Transfer Admittance | y _{fs} | V _{DS} = 10 V, I _D = 20 A | 11 | 22 | | S |
| | Drain Leakage Current | loss | V _{DS} = 60 V, V _{GS} = 0 V | | | 10 | μΑ |
| | Gate to Source Leakage Current | Igss | Vgs = ±20 V, Vps = 0 V | | | ±10 | μΑ |
| | Input Capacitance | Ciss | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | | 1500 | | pF |
| | Output Capacitance | Coss | | | 250 | | pF |
| | Reverse Transfer Capacitance | Crss | | | 120 | | pF |
| * | Turn-on Delay Time | td(on) | ID = 20 A, VGS(on) = 10 V, VDD = 30 V, | | 35 | | ns |
| * | Rise Time | tr | $R_G = 10 \Omega$ | | 320 | | ns |
| * | Turn-off Delay Time | td(off) | | | 89 | | ns |
| * | Fall Time | t _f | | | 120 | | ns |
| | Total Gate Charge | Q _G | ID = 40 A , VDD = 48 V, VGS = 10 V | | 30 | | nC |
| | Gate to Source Charge | Qgs | | | 5 | | nC |
| | Gate to Drain Charge | Q _{GD} | | | 8 | | nC |
| | Body Diode Forward Voltage | V _F (S-D) | IF = 40 A, VGS = 0 V | | 1.0 | | V |
| * | Reverse Recovery Time | trr | IF = 40 A, VGS = 0 V, | | 44 | | ns |
| * | Reverse Recovery Charge | Qrr | di/dt = 100 A/μs | | 60 | | nC |

TEST CIRCUIT 1 AVALANCHE CAPABILITY





TEST CIRCUIT 2 SWITCHING TIME

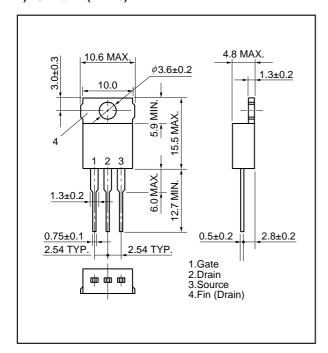


TEST CIRCUIT 3 GATE CHARGE

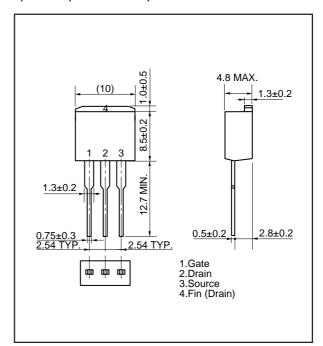


PACKAGE DRAWINGS (Unit: mm)

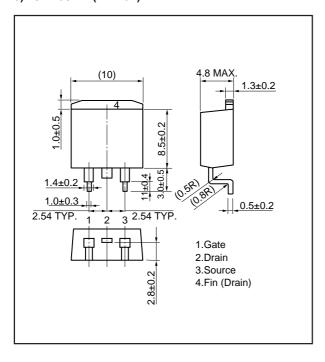
1) TO-220AB (MP-25)



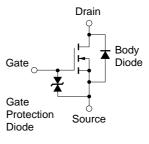
2) TO-262 (MP-25 Fin Cut)



3) TO-220SMD (MP-25Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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